

**100A, 55V, 0.008 Ohm, N-Channel, Power MOSFETs**

These are N-Channel enhancement mode silicon gate power field effect transistors. They are advanced power MOSFETs designed, tested, and guaranteed to withstand a specified level of energy in the breakdown avalanche mode of operation. All of these power MOSFETs are designed for applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. These types can be operated directly from integrated circuits.

**NOTE:** Calculated continuous current based on maximum allowable junction temperature. Package limited to 75A continuous, see Figure 9.

**Ordering Information**

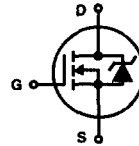
PART NUMBER	PACKAGE	BRAND
HRF3205	TO-220AB	HRF3205
HRF3205S	TO-263AB	HRF3205S

**NOTE:** When ordering, use the entire part number. Add the suffix T to obtain the TO-263AB variant in tape and reel, e.g., HRF3205ST.

**Features**

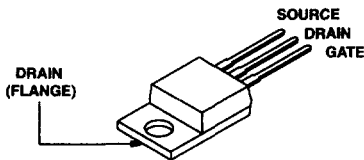
- 100A, 55V (See Note)
- Low On-Resistance,  $r_{DS(ON)} = 0.008\Omega$
- Temperature Compensating PSPICE® Model
- Thermal Impedance SPICE Model
- UIS Rating Curve
- Related Literature
  - TB334, "Guidelines for Soldering Surface Mount Components to PC Boards"

**Symbol**

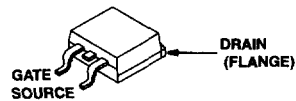


**Packaging**

JEDEC TO-220AB



JEDEC TO-263AB



**4**  
**N-CHANNEL**  
**STANDARD GATE**

## HRF3205, HRF3205S

### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

Drain to Source Voltage (Note 1)	$V_{DSS}$	55	V
Drain to Gate Voltage ( $R_{GS} = 20\text{k}\Omega$ ) (Note 1)	$V_{DGR}$	55	V
Gate to Source Voltage	$V_{GS}$	$\pm 20\text{V}$	V
Drain Current			
Continuous	$I_D$	100	A
Pulsed Drain Current (Note 2)	$I_{DM}$	390	A
Pulsed Avalanche Rating	$E_{AS}$	Figure 10	
Power Dissipation	$P_D$	175	W
Derate Above $25^\circ\text{C}$		1.17	$\text{W}/^\circ\text{C}$
Operating and Storage Temperature	$T_J, T_{STG}$	-55 to 175	$^\circ\text{C}$
Maximum Temperature for Soldering			
Leads at 0.063in (1.6mm) from Case for 10s	$T_L$	300	$^\circ\text{C}$
Package Body for 10s, See Techbrief 334	$T_{pkg}$	260	$^\circ\text{C}$

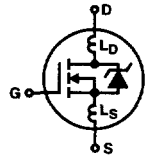
CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

#### NOTE:

- $T_J = 25^\circ\text{C}$  to  $150^\circ\text{C}$ .

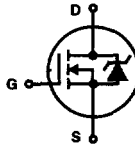
### Electrical Specifications $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS	
Drain to Source Breakdown Voltage	$BV_{DSS}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	55	-	-	V	
Gate to Source Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	2	-	4	V	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 55\text{V}, V_{GS} = 0\text{V}$	-	-	25	$\mu\text{A}$	
		$V_{DS} = 44\text{V}, V_{GS} = 0\text{V}, T_C = 150^\circ\text{C}$	-	-	250	$\mu\text{A}$	
Gate to Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20\text{V}$	-	-	100	nA	
Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS} / \Delta T_J$	Reference to $25^\circ\text{C}, I_D = 250\mu\text{A}$	-	0.057	-	V	
Drain to Source On Resistance	$r_{DS(ON)}$	$I_D = 59\text{A}, V_{GS} = 10\text{V}$ (Figure 4)	-	0.0065	0.008	$\Omega$	
Turn-On Delay Time	$t_{d(ON)}$	$V_{DD} = 28\text{V}, I_D = 59\text{A}, R_L = 0.47\Omega, V_{GS} = 10\text{V}, R_{GS} = 2.5\Omega$	-	14	-	ns	
Rise Time	$t_r$		-	100	-	ns	
Turn-Off Delay Time	$t_{d(OFF)}$		-	43	-	ns	
Fall Time	$t_f$		-	70	-	ns	
Total Gate Charge	$Q_g$	$V_{DD} = 44\text{V}, I_D = 59\text{A}, V_{GS} = 10\text{V}, I_g(\text{REF}) = 3\text{mA}$ (Figure 6)	-	-	170	nC	
Gate to Source Charge	$Q_{gs}$		-	-	32	nC	
Gate to Drain "Miller" Charge	$Q_{gd}$		-	-	74	nC	
Input Capacitance	$C_{ISS}$	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$ (Figure 5)	-	4000	-	pF	
Output Capacitance	$C_{OSS}$		-	1300	-	pF	
Reverse Transfer Capacitance	$C_{RSS}$		-	480	-	pF	
Internal Source Inductance	$L_S$	Measured From the Contact Screw on Tab to Center of Die	Modified MOSFET Symbol Showing the Internal Devices Inductances	-	7.5	-	nH
		Measured From the Drain Lead, 6mm (0.25in) From Package to Center of Die					
Internal Drain Inductance	$L_D$	Measured From the Source Lead, 6mm (0.25in) From Header to Source Bonding Pad		-	4.5	-	nH
Thermal Resistance Junction to Case	$R_{\theta JC}$		-	-	0.85	$^\circ\text{C}/\text{W}$	
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	TO-220	-	-	62	$^\circ\text{C}/\text{W}$	
		TO-263 (PCB Mount, Steady State)	-	-	40	$^\circ\text{C}/\text{W}$	



Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Continuous Source to Drain Current	$I_{SD}$	MOSFET Symbol Showing The Integral Reverse P-N Junction Diode	-	-	100 (Note 1)	A
Pulsed Source to Drain Current (Note 2)	$I_{SDM}$		-	-	390	A
Source to Drain Diode Voltage	$V_{SD}$	$I_{SD} = 59A$ (Note 4)	-	-	1.3	V
Reverse Recovery Time	$t_{rr}$	$I_{SD} = 59A, di_{SD}/dt = 100A/\mu s$ (Note 4)	-	110	170	ns
Reverse Recovered Charge	$Q_{RR}$	$I_{SD} = 59A, di_{SD}/dt = 100A/\mu s$ (Note 4)	-	450	680	nC



NOTE:

2. Repetitive rating; pulse width limited by maximum junction temperature (See Figure 11)

Typical Performance Curves

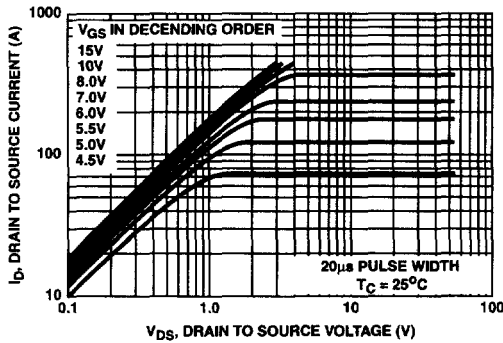


FIGURE 1. OUTPUT CHARACTERISTICS

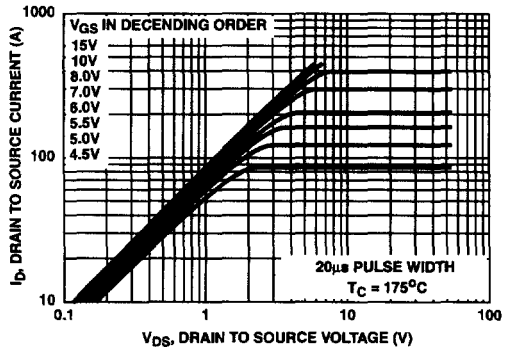


FIGURE 2. OUTPUT CHARACTERISTICS

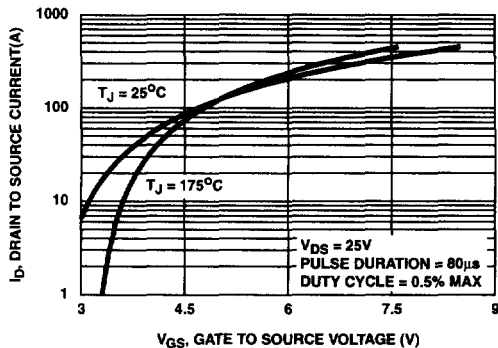


FIGURE 3. TRANSFER CHARACTERISTICS

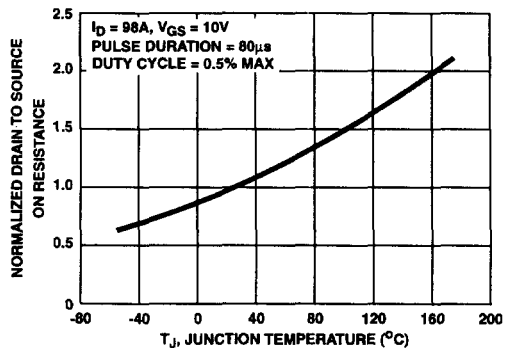


FIGURE 4. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

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Typical Performance Curves (Continued)

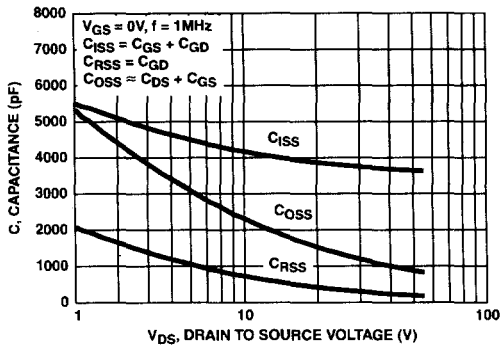


FIGURE 5. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE

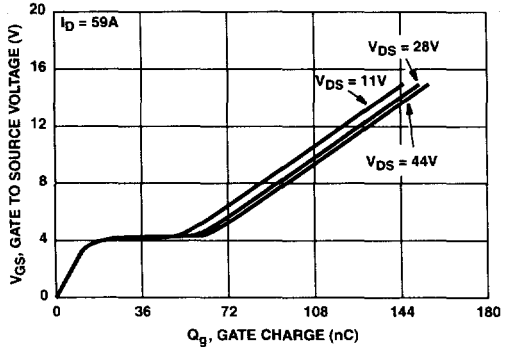


FIGURE 6. GATE CHARGE WAVEFORMS FOR CONSTANT GATE CURRENT

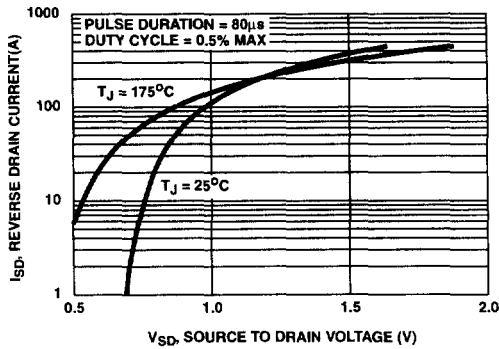


FIGURE 7. SOURCE TO DRAIN DIODE FORWARD VOLTAGE

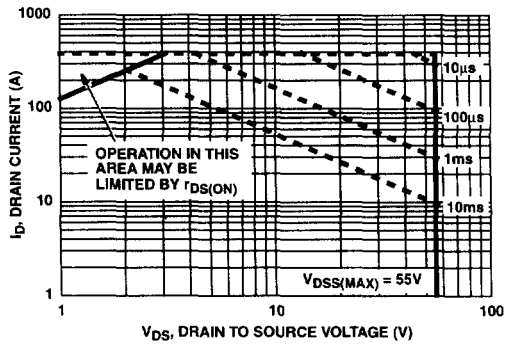


FIGURE 8. FORWARD BIAS SAFE OPERATING AREA

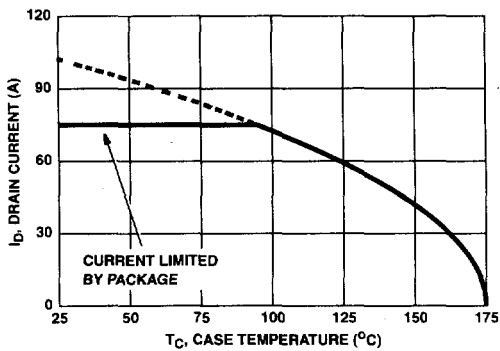


FIGURE 9. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

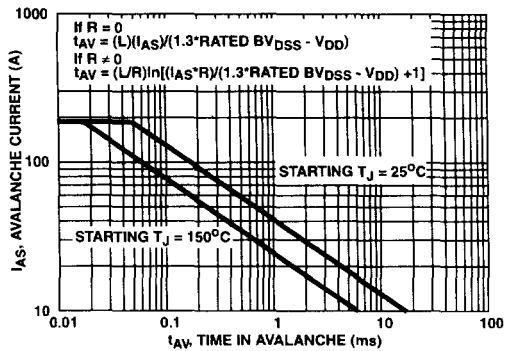


FIGURE 10. UNCLAMPED INDUCTIVE SWITCHING CAPABILITY

Typical Performance Curves (Continued)

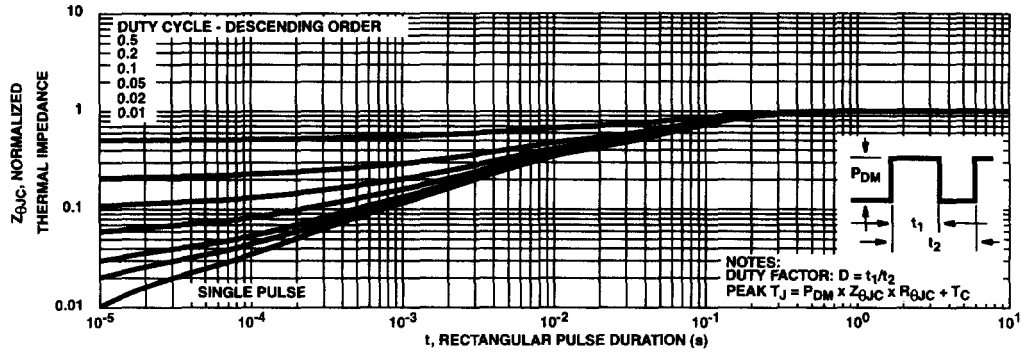


FIGURE 11. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

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